

#### 9.8 mΩ, Nanopower Mobile 6 A Load Switch with Discharge

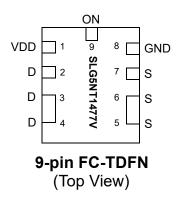
#### **General Description**

The SLG5NT1477V is a 9.8 m $\Omega$ , 6 A single-channel load switch that is able to switch 0.85 V to 3.3 V power rails. The product is packaged in an ultra-small 1.5 x 2.0 mm package.

#### **Features**

- 1.5 x 2.0 mm FC-TDFN 9L package (2 fused pins for drain and 2 fused pins for source)
- Logic level ON pin capable of supporting 0.85 V CMOS Logic
- · Discharged Load when off
- Fast Turn On time
- Low RDS<sub>ON</sub> while supporting 6 A
- Pb-Free / Halogen-Free / RoHS compliant
- Operating Temperature: -40 °C to 85 °C
- Operating Voltage: 3.0 V to 5.25 V

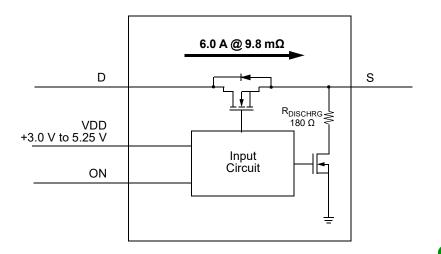
#### **Pin Configuration**



#### **Applications**

- · Watch Power Rail Switching
- Tablet Power Rail Switching
- Smartphone Power Rail Switching
- Notebook Power Rail Switching

#### **Block Diagram**



RoHS Compliant Directive 2002/95/EC



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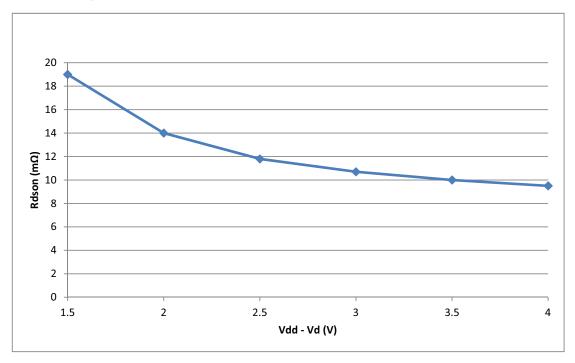
### **Pin Description**

Pin #	Pin Name	Туре	Pin Description
1	VDD	PWR	VDD power for load switch control (3.0 V to 5.25 V)
2	D	MOSFET	Drain of Power MOSFET
3	D	MOSFET	Drain of Power MOSFET (fused with pin 4)
4	D	MOSFET	Drain of Power MOSFET (fused with pin 3)
5	S	MOSFET	Source of Power MOSFET (fused with pin 6)
6	S	MOSFET	Source of Power MOSFET (fused with pin 5)
7	S	MOSFET	Source of Power MOSFET
8	GND	GND	Ground
9	ON	Input	Turns MOSFET ON (4 M $\Omega$ pull down resistor) CMOS input with ON_V <sub>IL</sub> < 0.2 V, ON_V <sub>IH</sub> > 0.85 V

#### **Ordering Information**

Part Number	Туре	Production Flow
SLG5NT1477V	FC-TDFN 9L	Industrial, -40 °C to 85 °C
SLG5NT1477VTR	FC-TDFN 9L (Tape and Reel)	Industrial, -40 °C to 85 °C

#### SLG5NT1477V RDS<sub>ON</sub>



Datasheet	Revision 1.29	2-Feb-2022
CFR0011-120-01	Page 2 of 12	©2022 Renesas Electronics Corporation



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#### **Absolute Maximum Ratings**

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply				7	V
T <sub>S</sub>	Storage Temperature		-65		150	°C
ESD <sub>HBM</sub>	ESD Protection	Human Body Model	2000			V
MSL	Moisture Sensitivity Level			,	1	
W <sub>DIS</sub>	Package Power Dissipation				1.0	W
MOSFET IDS <sub>PK</sub>	Peak Current from Drain to Source	For no more than 1 ms with 1% duty cycle			9	Α

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **Electrical Characteristics**

 $T_A = -40$  °C to 85 °C (unless otherwise noted)

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Power Supply Voltage	-40 °C to 85 °C	3.0		5.25	V
		when OFF, T <sub>A</sub> = 25 °C		30	60	nA
1	Dower Supply Current (DIN 1)	when ON, No load, ON = V <sub>DD</sub> , T <sub>A</sub> = 25 °C		3.0        30       35       100       200       16.2       11.5       9.5       7.9       7.4       19.2       14.1       10.5       9.7       9.2       18.33       13.65       11.96	70	nA
I <sub>DD</sub>	Power Supply Current (PIN T)	when OFF, T <sub>A</sub> = 70 °C		100	900	nA
		when ON, No load, ON = V <sub>DD</sub> , T <sub>A</sub> = 70 °C		200	900	nA
		$T_A = 25 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 1.5 \text{ V}$		16.2	18.6	mΩ
	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		11.5	13.2	mΩ	
DDQ	ON Desistance	$T_A = 25 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 2.5 \text{ V}$	3.0       3.0        30       35       100       200      /     16.2      /     16.2      /     11.5      /     9.5      /     7.9      /     7.9      /     19.2      /     14.1      /     10.5      /     9.7      /     9.2      /     18.33      /     15.21      /     13.65      /     11.96	9.5	10.9	mΩ
RDS <sub>ON</sub> (		$T_A = 25 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.0 \text{ V}$		8.5	9.8	mΩ
		$T_A = 25 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.5 \text{ V}$		7.9	9.1	mΩ
		$T_A = 25 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 4.0 \text{ V}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	8.5	mΩ	
		$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 1.5 \text{ V}$		19.2	22.1	mΩ
		$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 2.0 \text{ V}$		14.1	16.2	mΩ
DDS	ON Registeres	$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 2.5 \text{ V}$		5        30      35        100      9        200      9        16.2      1        11.5      1        9.5      1        8.5      9        7.9      9        7.4      8        19.2      2        14.1      1        10.5      1        9.7      1        9.7      1        9.7      1        9.7      1        9.7      1        9.7      1        9.7      1        9.7      1        13.65      19        15.21      17        13.65      19        12.61      14        11.96      13	13.5	mΩ
RDS <sub>ON</sub>	ON Resistance	$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.0 \text{ V}$			12.1	mΩ
		$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.5 \text{ V}$			11.2	mΩ
		$T_A = 70 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 4.0 \text{ V}$		9.2	10.6	mΩ
		$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 1.5 \text{ V}$		24.96	28.73	mΩ
		$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 2.0 \text{ V}$		18.33	21.06	mΩ
RDS <sub>ON</sub>	ON Posistanco	$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 2.5 \text{ V}$		15.21	17.55	mΩ
RD3 <sub>ON</sub>	ON Resistance	$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.0 \text{ V}$		13.65	15.73	mΩ
		$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 3.5 \text{ V}$		12.61	14.56	mΩ
		$T_A = 85 \text{ °C}; I_{DS} = 300 \text{ mA}, V_{DD} - V_D = 4.0 \text{ V}$		11.96	13.78	mΩ
IOSFET IDS	Current from D to S	Continuous			6	А
V <sub>D</sub>	Drain Voltage		0.85		V <sub>DD</sub> - 1.5	V



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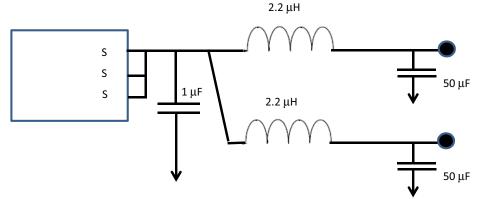
#### **Electrical Characteristics (continued)**

 $T_A = -40$  °C to 85 °C (unless otherwise noted)

Parameter	Description	Conditions	Min.	Тур.	Max.	Unit
			7	9	12	μs
T <sub>Total_ON</sub>	Total Turn On Time	50% ON to 90% V <sub>S</sub> , V <sub>DD</sub> = 5.25 V, V <sub>D</sub> = 1.0 V, C <sub>LOAD</sub> = 2 $\mu$ F, R <sub>LOAD</sub> = 20 $\Omega$	8	10	12	μs
		50% ON to 90% V <sub>S</sub> , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, C <sub>LOAD</sub> = 2 x (50 $\mu$ F + 2.2 $\mu$ H Inductor) <sup>2</sup>	30	7  9    3  10    0  42    30  160    50  176    0  26    -  -    00  180    85	50	μs
V <sub>S(SR)</sub>		10% V <sub>S</sub> to 90% V <sub>S</sub> , V <sub>DD</sub> = 5.25 V, V <sub>D</sub> = 1.0 V, C <sub>LOAD</sub> = 10 μF, R <sub>LOAD</sub> = 20 Ω	130	160	190	V/ms
	V <sub>S</sub> Slew Rate	10% V <sub>S</sub> to 90% V <sub>S</sub> , V <sub>DD</sub> = 5.25 V, V <sub>D</sub> = 1.0 V, C <sub>LOAD</sub> = 2 $\mu$ F, R <sub>LOAD</sub> = 20 $\Omega$	150	176	200	V/ms
		10% V <sub>S</sub> to 90% V <sub>S</sub> , V <sub>DD</sub> = 5 V, V <sub>D</sub> = 1.0 V, R <sub>LOAD</sub> = 20 Ω, C <sub>LOAD</sub> = 2 x (50 μF + 2.2 μH Inductor) <sup>2</sup>	20	26	35	V/ms
C <sub>LOAD</sub>	Output Load Capacitance	C <sub>LOAD</sub> connected from S to GND			10	μF
R <sub>DISCHRG</sub>	Discharge Resistance		100	180	300	Ω
$ON_V_{IH}$	High Input Voltage on ON pin		0.85		V <sub>DD</sub>	V
$ON_V_{IL}$	Low Input Voltage on ON pin		-0.3	0	0.2	V
T <sub>OFF_Delay</sub>	OFF Delay Time	50% ON to V <sub>S</sub> Fall Start ↓, V <sub>DD</sub> = 5.25 V, V <sub>D</sub> = 1.0 V, R <sub>LOAD</sub> = 20 Ω, no C <sub>LOAD</sub>			60	μs
T <sub>FALL</sub>	V <sub>S</sub> Fall Time	90% V <sub>S</sub> to 10% V <sub>S</sub> , V <sub>DD</sub> = 5.25 V, V <sub>D</sub> = 1.0 V, R <sub>LOAD</sub> = 20 Ω, no C <sub>LOAD</sub>		15		μs

2. See Application Diagram below regarding  $C_{LOAD}$  = 2 x (50  $\mu$ F + 2.2  $\mu$ H).

#### Application Diagram (Source loading > 10 μF)



Capacitive loads > 10  $\mu$ F directly on the S pin may result in nonlinear output ramping. In cases where > 10  $\mu$ F load capacitance is required, we recommend decoupling the load(s) with 2.2  $\mu$ H inductors while putting a 1  $\mu$ F capacitor on S as shown above in order to guarantee linear ramping and inrush current limiting.

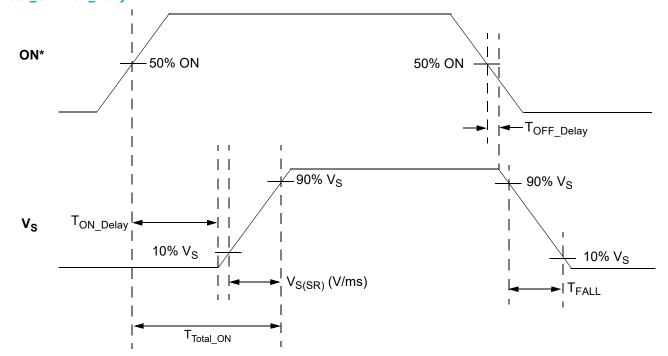
Datasheet	Revision 1.29	2-Feb-2022
	Page 4 of 12	©2000 Denses Electronice Ormanetica

## RENESAS

## SLG5NT1477V

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### T<sub>Total\_ON</sub>, T<sub>ON\_Delay</sub> and Slew Rate Measurement



<sup>\*</sup>Rise and Fall Times of the ON Signal are 100 ns

D	at	a	s	h	e	e	t
-	~	-	-		•	-	•

## 9.8 m $\Omega$ , Nanopower Mobile 6 A Load Switch with Discharge

#### Layout Guidelines:

- 1. The VDD pin needs a 0.1 µF and 10 µF external capacitors to smooth pulses from the power supply. Locate these capacitors as close as possible to the SLG5NT1477V's PIN1.
- 2. Since the D and S pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with <u>absolute minimum</u> <u>widths</u> of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 1, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;
- 3. To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input  $C_{IN}$  and output  $C_{LOAD}$  low-ESR capacitors as close as possible to the SLG5NT1477V's D and S pins;
- 4. The GND pin should be connected to system analog or power ground plane.
- 5. 2 oz. copper is recommended for high current operation.

#### SLG5NT1477V Evaluation Board:

A GreenFET Evaluation Board for SLG5NT1477V is designed according to the statements above and is illustrated on Figure 1. Please note that evaluation board has D\_Sense and S\_Sense pads. They cannot carry high currents and dedicated only for RDS<sub>ON</sub> evaluation.

Please solder your SLG5NT1477V here

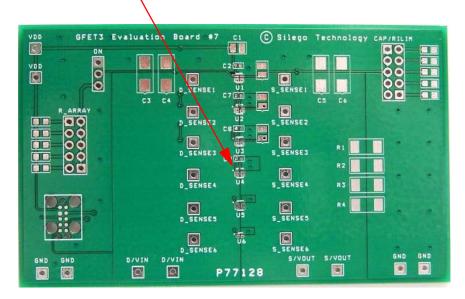
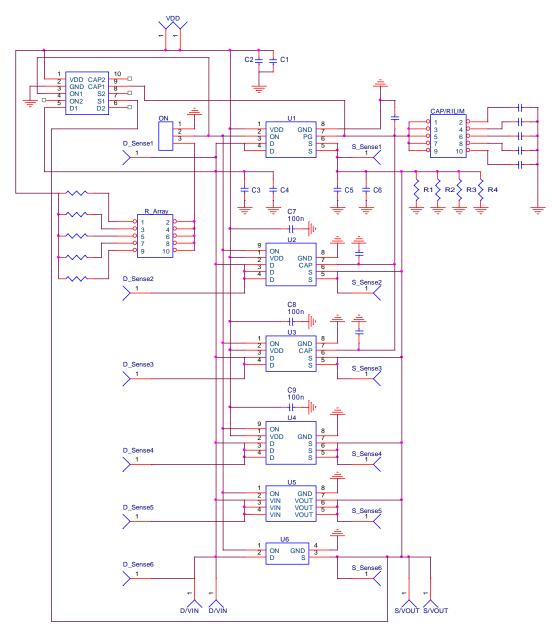


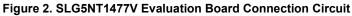
Figure 1. SLG5NT1477V Evaluation Board

<b>D</b>	4 1		- 4
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9.8 m $\Omega$ , Nanopower Mobile 6 A Load Switch with Discharge





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#### **Basic Test Setup and Connections**

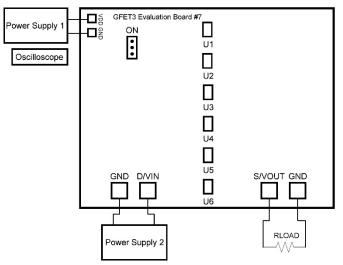
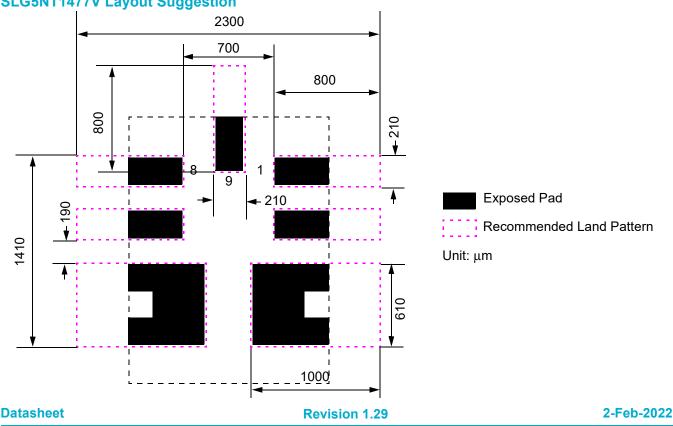


Figure 3. SLG5NT1477V Evaluation Board Connection Circuit

#### **EVB** Configuration

- 1. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
- 2. Turn on Power Supply 1 and set desired V<sub>DD</sub> from 3 V...5.25 V range;
- 3. Turn on Power Supply 2 and set desired V<sub>D</sub> from 0.85 V...V<sub>DD</sub> 1.5 V range;
- 4. Toggle the ON signal High or Low to observe SLG5NT1477V operation.

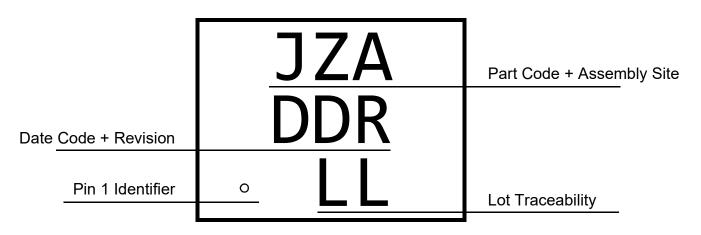


#### SLG5NT1477V Layout Suggestion



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#### Package Top Marking System Definition



JZ - Part Code<sup>1</sup> A - Assembly Site Code Field<sup>2</sup> DD - Date Code Field<sup>1</sup> R - Part Revision Code Field<sup>2</sup> LL - Lot Traceability Field<sup>1</sup>

Note 1: Each character in code field can be alphanumeric A-Z and 0-9 Note 2: Character in code field can be alphabetic A-Z

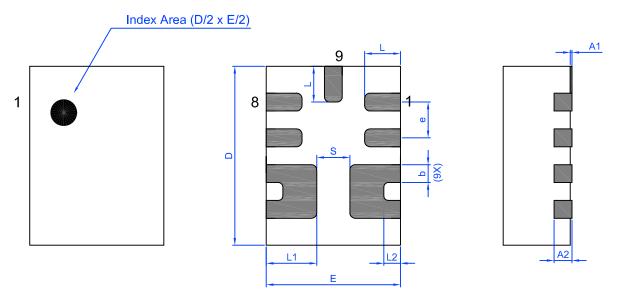
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#### **Package Drawing and Dimensions**

9 Lead TDFN FC Package 1.5 x 2.0 mm (Fused Lead) JEDEC MO-252, Variation W2015D





Unit: mm								
Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max	
A	0.70	0.75	0.80	L	0.35	0.40	0.45	
A1	0.005	-	0.060	L1	0.515	0.565	0.615	
A2	0.15	0.20	0.25	L2	0.135	0.185	0.235	
b	0.15	0.20	0.25	е	0.40 BSC			
D	1.95	2.00	2.05	S	0.37 REF			
E	1.45	1.50	1.55					

Datasheet	



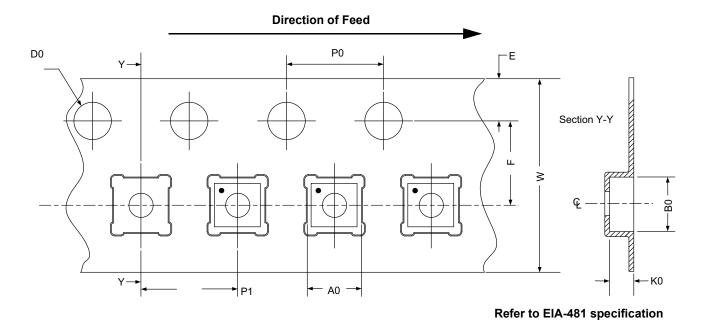
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#### **Tape and Reel Specifications**

Deekers # of		Nominal	Max Units		Reel &	Leader (min)		Trailer (min)		Таре	Part
Package Type	# of Pins	Package Size [mm]	per Reel	per Box	Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
TDFN 9L FC Green	9	1.5 x 2.0 x 0.75	3000	3000	178 / 60	100	400	100	400	8	4

#### **Carrier Tape Drawing and Dimensions**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	B0	K0	P0	P1	D0	E	F	W
TDFN 9L FC Green	1.70 ±0.05 mm	2.20 ±0.05 mm	0.95 +0.10 mm -0.05 mm	4	4	1.5	1.75	3.5	8



**Recommended Reflow Soldering Profile** 

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 2.25 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.

Datasheet	Revision 1.29	2-Feb-2022
CFR0011-120-01	Page 11 of 12	©2022 Renesas Electronics Corporation



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#### **Revision History**

Date	Version	Change
2/2/2022	1.29	Updated Company name and logo Fixed typos
11/3/2020	1.28	Updated Carrier Tape Drawing and Dimensions
6/5/2020	1.27	Updated style and formatting Added Layout Guidelines Add Tape and Reel Feed Direction Fixed typos
9/8/2016	1.26	Updated T <sub>Total_ON</sub> , V <sub>OUT(SR)</sub> , T <sub>OFF_Delay</sub> , T <sub>FALL</sub> specs Updated Application Diagram Notes Updated Formating and Parameter Names for clarity
4/26/2016	1.25	Added MSL 1 Added Part Code Marking Information
9/04/2015	1.24	Fixed T <sub>A</sub> conditions in Electrical Characteristics

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